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**INTEGRATED CIRCUITS, SILICON MONOLITHIC, PULSE
WIDTH MODULATOR**

BASED ON TYPE ST1843

Detail Specification No. 9108/020

Issue 5	April 2022
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DCR No.	CHANGE DESCRIPTION
1500	Specification updated to incorporate changes per DCR.

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1 GENERAL

1.1 SCOPE

This specification details the ratings, physical and electrical characteristics and test and inspection data for the component type variants and/or the range of components specified below. It supplements the requirements of, and shall be read in conjunction with, the ESCC Generic Specification listed under Applicable Documents.

1.2 APPLICABLE DOCUMENTS

The following documents form part of this specification and shall be read in conjunction with it:

- (a) ESCC Generic Specification No. [9000](#).
- (b) [MIL-STD-883](#), Test Methods and Procedures for Microelectronics.

1.3 TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESCC Basic Specification No. [21300](#) shall apply.

1.4 THE ESCC COMPONENT NUMBER AND COMPONENT TYPE VARIANTS

1.4.1 The ESCC Component Number

The ESCC Component Number shall be constituted as follows:

Example: 910802001F

- Detail Specification Reference: 9108020
- Component Type Variant Number: 01 (as required)
- Total Dose Radiation Level Letter: F (as required)

1.4.2 Component Type Variants

The component type variants applicable to this specification are as follows:

Variant Number	Based on Type	Case	Terminal Material and Finish	Weight max g	Total Dose Radiation Level Letter
01	ST1843	FP	G2	0.45	F [50krad(Si)]
02	ST1843	FP	G4	0.45	F [50krad(Si)]

The terminal material and finish shall be in accordance with the requirements of ESCC Basic Specification No. [23500](#).

Total dose radiation level letters are defined in ESCC Basic Specification No. [22900](#). If an alternative radiation test level is specified in the Purchase Order the letter shall be changed accordingly.

1.5 MAXIMUM RATINGS

The maximum ratings shall not be exceeded at any time during use or storage.

Maximum ratings shall only be exceeded during testing to the extent specified in this specification and when stipulated in Test Methods and Procedures of the ESCC Generic Specification.

Characteristics	Symbols	Maximum Ratings	Units	Remarks
Supply Voltage (low impedance source)	V_i	30	V	Note 1
Supply Current	I_i	30	mA	Notes 1, 2
Output Current	I_o	± 1	A	Note 1
Output Energy (capacitive load)	E_o	5	μJ	
Analogue Inputs	-	-0.3 to 5.5	V	Pins 2, 3
Error Amplifier Output Sink Current	$I_{o\text{-SINK}}$	10	mA	Note 1
Operating Temperature Range	T_{op}	-55 to +125	$^{\circ}\text{C}$	T_{amb}
Storage Temperature Range	T_{stg}	-65 to +150	$^{\circ}\text{C}$	
Junction Temperature	T_j	+150	$^{\circ}\text{C}$	
Soldering Temperature	T_{sol}	+265	$^{\circ}\text{C}$	Note 3

NOTES:

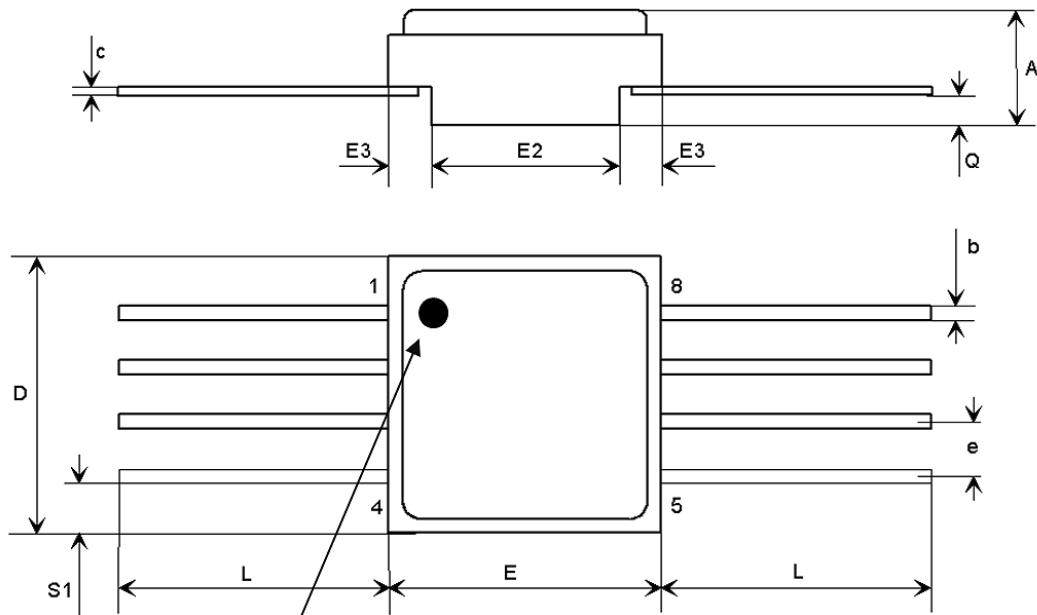
1. All voltages are with respect to Ground, all currents are positive into the specified terminal.
2. Supply voltage is self-limited by Zener clamp.
3. Duration 10 seconds maximum at a distance of not less than 1.5mm from the device body and the same terminal shall not be resoldered until 3 minutes have elapsed.

1.6 HANDLING PRECAUTIONS

These devices are susceptible to damage by electrostatic discharge. Therefore, suitable precautions shall be employed for protection during all phases of manufacture, testing, packaging, shipment and any handling.

These components are categorised as Class 2 per ESCC Basic Specification No. [23800](#) with a Minimum Critical Path Failure Voltage of 2000 Volts.

1.7 PHYSICAL DIMENSIONS AND TERMINAL IDENTIFICATION
Flat Package (FP) - 8 Pin



Note 1

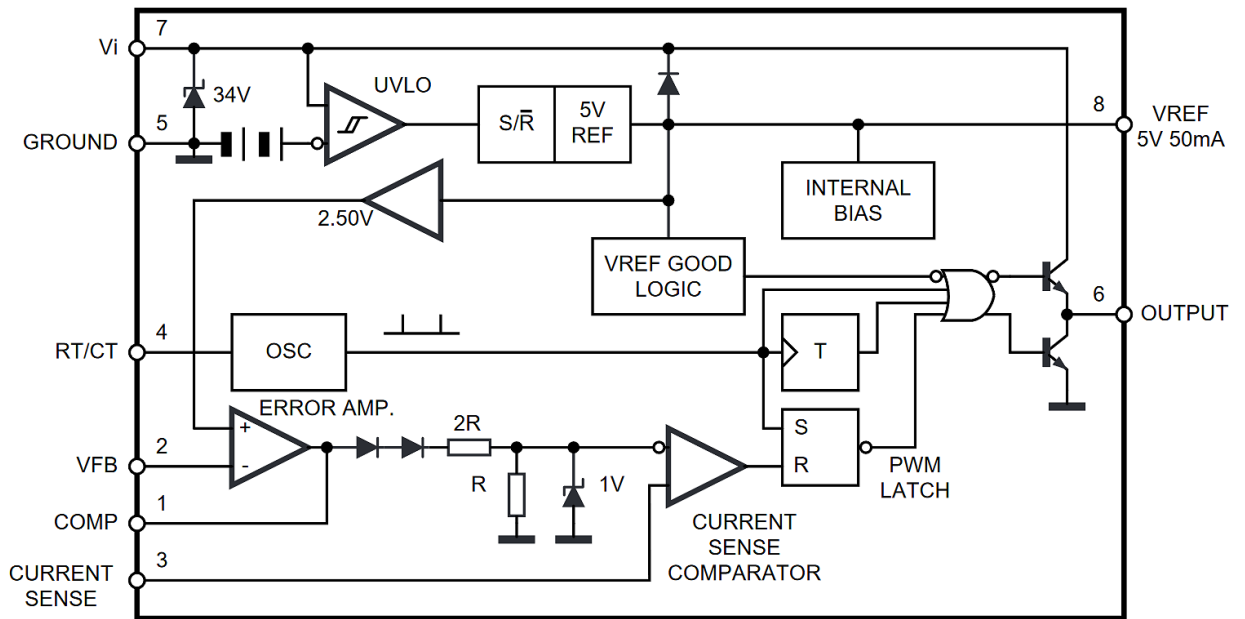
Symbols	Dimensions mm		Notes
	Min	Max	
A	2.24	2.64	
b	0.38	0.48	2
c	0.1	0.16	2
D	6.35	6.61	
E	6.35	6.61	
E2	4.32	4.58	
E3	0.88	1.14	
e	1.27 BSC		3
L	6.51	7.38	2
Q	0.66	0.92	
S1	0.92	1.32	4

NOTES:

1. Terminal identification shall be by means of a notch or a dot located adjacent to Pin 1.
2. Applies to all pins.
3. 6 places.
4. 4 places.

1.8 **FUNCTIONAL DIAGRAM**

Note: For the ST1843 the toggle flip-flop is unused.



1.9 **PIN ASSIGNMENT**

Pin	Name	Description
1	COMP	This pin is the Error Amplifier output and is made available for loop compensation.
2	V _{FB}	This is the inverting input of the Error Amplifier. It is normally connected to the switching power supply output through a resistor divider.
3	I _{SENSE}	A voltage proportional to inductor current is connected to this input. The PWM uses this information to terminate the output switch conduction.
4	R _T /C _T	The oscillator frequency and maximum Output duty cycle are programmed by connecting resistor R _T to V _{ref} and capacitor C _T to ground. Operation to 500kHz is possible.
5	GROUND	This pin is the combined control circuitry and power ground.
6	OUTPUT	This output directly drives the gate of a power MOSFET. Peak currents up to 1A are sourced and sunk by this pin.
7	V _i	This pin is the positive supply of the control IC.
8	V _{ref}	This is the reference output. It provides charging current for capacitor C _T through resistor R _T .

2 REQUIREMENTS

2.1 GENERAL

The complete requirements for procurement of the components specified herein are as stated in this specification and the ESCC Generic Specification. Permitted deviations from the Generic Specification, applicable to this specification only, are listed below.

Permitted deviations from the Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESCC requirement and do not affect the component's reliability, are listed in the appendices attached to this specification.

2.1.1 Deviations from the Generic Specification

None.

2.2 MARKING

The marking shall be in accordance with the requirements of ESCC Basic Specification No. 21700 and as follows.

The information to be marked on the component shall be:

- (a) Terminal identification.
- (b) The ESCC qualified components symbol (for ESCC qualified components only).
- (c) The ESCC Component Number (see Para. 1.4.1).
- (d) Traceability information.

2.3 ELECTRICAL MEASUREMENTS AT ROOM, HIGH AND LOW TEMPERATURES

Electrical measurements shall be performed at room, high and low temperatures. Consolidated Notes are given in Para. 2.3.3.

2.3.1 Room Temperature Electrical Measurements

The measurements shall be performed at $T_{amb} = +22 \pm 3^{\circ}C$.

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions	Limits		Units
				Min	Max	
REFERENCE SECTION						
Output Voltage	V_{REF}	-	$V_i = 15V$ $R_T = 10k\Omega, C_T = 3.3nF$ $I_o = 1mA$	4.95	5.05	V
Line regulation	ΔV_{REF_LINE}	-	$12V \leq V_i \leq 25V$ $R_T = 10k\Omega, C_T = 3.3nF$	-	20	mV
Load Regulation	ΔV_{REF_LOAD}	-	$V_i = 15V$ $R_T = 10k\Omega, C_T = 3.3nF$ $1mA \leq I_o \leq 20mA$	-	25	mV
Output Short Circuit Current	I_{SC}	3011	$V_i = 15V$ $R_T = 10k\Omega, C_T = 3.3nF$	-180	-30	mA

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions	Limits		Units
				Min	Max	
OSCILLATOR SECTION						
Frequency	f_{osc}	-	$V_i = 15V$ $R_T = 10k\Omega, C_T = 3.3nF$	49	55	kHz
Frequency Change with Voltage	$\Delta f_{osc}/\Delta V$	-	$12V \leq V_i \leq 25V$ $R_T = 10k\Omega, C_T = 3.3nF$	-1	1	%
Discharge Current	I_{DISCHG}	-	$V_i = 15V$ $R_T = 10k\Omega, C_T = 3.3nF$ $V_{OSC} = 2V$	8.1	8.8	mA
ERROR AMP SECTION						
Input Voltage	V_2	-	$V_i = 15V$ $R_T = 10k\Omega, C_T = 3.3nF$ $V_{PIN1} = 2.5V$	2.45	2.55	V
Input Bias Current	I_b	4001	$V_i = 15V$ $R_T = 10k\Omega, C_T = 3.3nF$ $V_{FB} = 5V$	-1	1	μA
Open Loop Voltage Gain	A_{VOL}	-	$V_i = 15V$ $R_T = 10k\Omega, C_T = 3.3nF$ $2V \leq V_o \leq 4V$	65	-	dB
Power Supply Rejection Ratio	PSRR	4003	$12V \leq V_i \leq 25V$ $R_T = 10k\Omega, C_T = 3.3nF$	68	-	dB
Output Sink Current	I_{O_SINK}	-	$V_i = 15V$ $R_T = 10k\Omega, C_T = 3.3nF$ $V_{PIN2} = 2.7V$ $V_{PIN1} = 1.1V$	6	-	mA
Output Source Current	I_{O_SOURCE}	-	$V_i = 15V$ $R_T = 10k\Omega, C_T = 3.3nF$ $V_{PIN2} = 2.3V$ $V_{PIN1} = 5V$	-	-1	mA
V_{OUT} High	V_{OH}	-	$V_i = 15V$ $R_T = 10k\Omega, C_T = 3.3nF$ $V_{PIN2} = 2.3V$ $R_L = 15k\Omega$ to GROUND	5.4	-	V
V_{OUT} Low	V_{OL}	-	$V_i = 15V$ $R_T = 10k\Omega, C_T = 3.3nF$ $V_{PIN2} = 2.3V$ $R_L = 15k\Omega$ to V_{ref}	-	950	mV

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions	Limits		Units
				Min	Max	
CURRENT SENSE SECTION						
Gain	G_V	4004	$V_i = 15V$ $R_T = 10k\Omega, C_T = 3.3nF$ Notes 1, 2	2.85	3.15	V/V
Maximum Input Signal	V_3	-	$V_i = 15V$ $R_T = 10k\Omega, C_T = 3.3nF$ $V_{PIN1} = 2.3V$ Note 1	0.9	1.05	V
Supply Voltage Rejection	SVR	-	$12V \leq V_i \leq 25V$ $R_T = 10k\Omega, C_T = 3.3nF$ Note 1	74	-	dB
Input Bias Current	I_b	4001	$V_i = 15V$ $R_T = 10k\Omega, C_T = 3.3nF$	-10	10	μA
Delay to output	d_o	3003	$V_i = 15V$ $R_T = 10k\Omega, C_T = 3.3nF$	-	300	ns
OUTPUT SECTION						
Output Low Level	V_{OL1}	3007	$V_i = 15V$ $R_T = 10k\Omega, C_T = 3.3nF$ $I_{SINK} = 20mA$	-	260	mV
Output Low Level	V_{OL2}	3007	$V_i = 15V$ $R_T = 10k\Omega, C_T = 3.3nF$ $I_{SINK} = 200mA$	-	2.2	V
Output High level	V_{OH1}	3006	$V_i = 15V$ $R_T = 10k\Omega, C_T = 3.3nF$ $I_{SOURCE} = 20mA$	13	-	V
Output High Level	V_{OH2}	3006	$V_i = 15V$ $R_T = 10k\Omega, C_T = 3.3nF$ $I_{SOURCE} = 200mA$	12	-	V
UVLO Saturation	V_{OLS}	-	$V_i = 6V$ $R_T = 10k\Omega, C_T = 3.3nF$ $I_{SINK} = 1mA$	-	1.1	V
Rise Time	t_r	3004	$V_i = 15V$ $R_T = 10k\Omega, C_T = 3.3nF$ $C_L = 1nF$	-	150	ns
Fall Time	t_f	3004	$V_i = 15V$ $R_T = 10k\Omega, C_T = 3.3nF$ $C_L = 1nF$	-	150	ns
UNDER-VOLTAGE LOCKOUT SECTION						
Start Threshold	V_{TH}	-	$V_i = 15V$ $R_T = 10k\Omega, C_T = 3.3nF$	7.8	9	V
Min Operating Voltage after Turn-on	V_{MIN}	-	$V_i = 15V$ $R_T = 10k\Omega, C_T = 3.3nF$	7	8.2	V
Max Duty Cycle	DC_{MAX}	-	$V_i = 15V$ $R_T = 10k\Omega, C_T = 3.3nF$	94	100	%
Min Duty Cycle	DC_{MIN}	-	$V_i = 15V$ $R_T = 10k\Omega, C_T = 3.3nF$	-	0	%

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions	Limits		Units
				Min	Max	
TOTAL STAND-BY CURRENT						
Start-up current	I _{ST}	-	V _i = 6.5V R _T = 10kΩ, C _T = 3.3nF	-	500	μA
Operating Supply Current	I _i	3005	V _i = 15V R _T = 10kΩ, C _T = 3.3nF V _{PIN2} = V _{PIN3} = 0V	-	17	mA
Zener Voltage	V _{IZ}	-	V _i = 15V R _T = 10kΩ, C _T = 3.3nF I _i = 25mA	30	-	V

2.3.2 High and Low Temperatures Electrical Measurements

The measurements shall be performed at T_{amb} = +125 (+0 -5)°C and T_{amb} = -55 (+5 -0)°C.

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions	Limits		Units
				Min	Max	
REFERENCE SECTION						
Output Voltage	V _{REF}	-	V _i = 15V R _T = 10kΩ, C _T = 3.3nF I _O = 1mA	4.8	5.05	V
Line regulation	ΔV _{REF_LINE}	-	12V ≤ V _i ≤ 25V R _T = 10kΩ, C _T = 3.3nF	-	220	mV
Load Regulation	ΔV _{REF_LOAD}	-	V _i = 15V R _T = 10kΩ, C _T = 3.3nF 1mA ≤ I _O ≤ 20mA	-	25	mV
Output Short Circuit Current	I _{SC}	3011	V _i = 15V R _T = 10kΩ, C _T = 3.3nF	-180	-30	mA
OSCILLATOR SECTION						
Frequency	f _{OSC}	-	V _i = 15V R _T = 10kΩ, C _T = 3.3nF	49	56	kHz
Frequency Change with Voltage	Δf _{OSC} /ΔV	-	12V ≤ V _i ≤ 25V R _T = 10kΩ, C _T = 3.3nF	-10	+10	%
Discharge Current	I _{DISCHG}	-	V _i = 15V R _T = 10kΩ, C _T = 3.3nF V _{OSC} = 2V	7.2	8.8	mA

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions	Limits		Units
				Min	Max	
ERROR AMP SECTION						
Input Voltage	V ₂	-	V _i = 15V R _T = 10kΩ, C _T = 3.3nF V _{PIN1} = 2.5V	2.4	2.55	V
Input Bias Current	I _b	4001	V _i = 15V R _T = 10kΩ, C _T = 3.3nF V _{FB} = 5V	-1	1	μA
Open Loop Voltage Gain	A _{VOL}	-	V _i = 15V R _T = 10kΩ, C _T = 3.3nF 2V ≤ V _O ≤ 4V	65	-	dB
Power Supply Rejection Ratio	PSRR	4003	12V ≤ V _i ≤ 25V R _T = 10kΩ, C _T = 3.3nF	40	-	dB
Output Sink Current	I _{O_SINK}	-	V _i = 15V R _T = 10kΩ, C _T = 3.3nF V _{PIN2} = 2.7V V _{PIN1} = 1.1V	2	-	mA
Output Source Current	I _{O_SOURCE}	-	V _i = 15V R _T = 10kΩ, C _T = 3.3nF V _{PIN2} = 2.3V V _{PIN1} = 5V	-	-500	μA
V _{OUT} High	V _{OH}	-	V _i = 15V R _T = 10kΩ, C _T = 3.3nF V _{PIN2} = 2.3V R _L = 15kΩ to GROUND	5	-	V
V _{OUT} Low	V _{OL}	-	V _i = 15V R _T = 10kΩ, C _T = 3.3nF V _{PIN2} = 2.3V R _L = 15kΩ to V _{ref}	-	1.1	V
CURRENT SENSE SECTION						
Gain	G _V	4004	V _i = 15V R _T = 10kΩ, C _T = 3.3nF Notes 1, 2	2.85	3.15	V/V
Maximum Input Signal	V ₃	-	V _i = 15V R _T = 10kΩ, C _T = 3.3nF V _{PIN1} = 2.3V Note 1	0.9	1.1	V
Supply Voltage Rejection	SVR	-	12V ≤ V _i ≤ 25V R _T = 10kΩ, C _T = 3.3nF Note 1	50	-	dB
Input Bias Current	I _b	4001	V _i = 15V R _T = 10kΩ, C _T = 3.3nF	-10	10	μA
Delay to output	d _o	3003	V _i = 15V R _T = 10kΩ, C _T = 3.3nF	-	300	ns

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions	Limits		Units
				Min	Max	
OUTPUT SECTION						
Output Low Level	V _{OL1}	3007	V _i = 15V R _T = 10kΩ, C _T = 3.3nF I _{SINK} = 20mA	-	400	mV
Output Low Level	V _{OL2}	3007	V _i = 15V R _T = 10kΩ, C _T = 3.3nF I _{SINK} = 200mA	-	2.2	V
Output High level	V _{OH1}	3006	V _i = 15V R _T = 10kΩ, C _T = 3.3nF I _{SOURCE} = 20mA	13	-	V
Output High Level	V _{OH2}	3006	V _i = 15V R _T = 10kΩ, C _T = 3.3nF I _{SOURCE} = 200mA	12	-	V
UVLO Saturation	V _{OLS}	-	V _i = 6V R _T = 10kΩ, C _T = 3.3nF I _{SINK} = 1mA	-	1.1	V
Rise Time	t _r	3004	V _i = 15V R _T = 10kΩ, C _T = 3.3nF C _L = 1nF	-	150	ns
Fall Time	t _f	3004	V _i = 15V R _T = 10kΩ, C _T = 3.3nF C _L = 1nF	-	150	ns
UNDER-VOLTAGE LOCKOUT SECTION						
Start Threshold	V _{TH}	-	V _i = 15V R _T = 10kΩ, C _T = 3.3nF	7.8	9	V
Min Operating Voltage after Turn-on	V _{MIN}	-	V _i = 15V R _T = 10kΩ, C _T = 3.3nF	7	8.2	V
Max Duty Cycle	DC _{MAX}	-	V _i = 15V R _T = 10kΩ, C _T = 3.3nF	94	100	%
Min Duty Cycle	DC _{MIN}	-	V _i = 15V R _T = 10kΩ, C _T = 3.3nF	-	0	%
TOTAL STAND-BY CURRENT						
Start-up current	I _{ST}	-	V _i = 6.5V R _T = 10kΩ, C _T = 3.3nF	-	500	μA
Operating Supply Current	I _i	3005	V _i = 15V R _T = 10kΩ, C _T = 3.3nF V _{PIN2} = V _{PIN3} = 0V	-	17	mA
Zener Voltage	V _{IZ}	-	V _i = 15V R _T = 10kΩ, C _T = 3.3nF I _i = 25mA	30	-	V

2.3.3 Notes to Electrical Measurement Tables

1. This parameter shall be measured at trip point of latch with V_{PIN2} = 0V.
2. The gain, A, is defined as follows:

$$A = \frac{\Delta V_{PIN1}}{\Delta V_{PIN3}} \cdot 0V \leq V_{PIN3} \leq 0.8V.$$

2.4 PARAMETER DRIFT VALUES

Unless otherwise specified, the measurements shall be performed at $T_{amb} = +22 \pm 3^{\circ}\text{C}$.

The test methods and test conditions shall be as per the corresponding test defined in Para. 2.3.1 Room Temperature Electrical Measurements.

The drift values (Δ) shall not be exceeded for each characteristic specified. The corresponding absolute limit values for each characteristic shall not be exceeded.

Characteristics	Symbols	Limits			Units
		Drift Value Δ	Absolute		
			Min	Max	
Operating Supply Current	I_i	± 0.25	-	17	mA
Output Voltage	V_{REF}	± 0.025	4.95	5.05	V
Output Low Level	V_{OL2}	± 0.05	-	2.2	V
Output High Level	V_{OH2}	± 0.05	12	-	V

2.5 INTERMEDIATE AND END-POINT ELECTRICAL MEASUREMENTS

Unless otherwise specified, the measurements shall be performed at $T_{amb} = +22 \pm 3^{\circ}\text{C}$.

The test methods and test conditions shall be as per the corresponding test defined in Para. 2.3.1 Room Temperature Electrical Measurements.

The drift values (Δ) shall not be exceeded for each characteristic where specified. The corresponding absolute limit values for each characteristic shall not be exceeded.

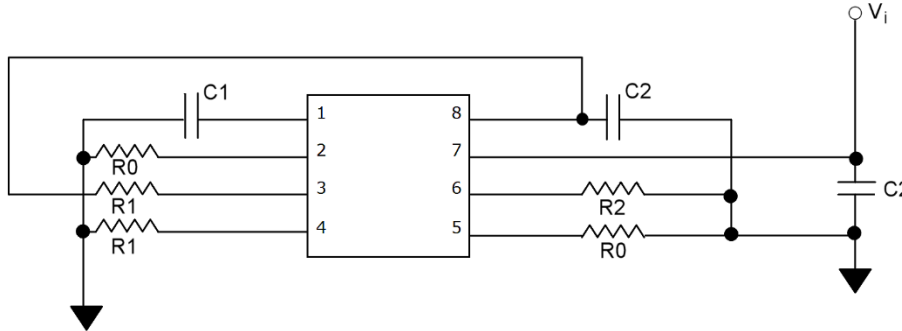
Characteristics	Symbols	Limits			Units
		Drift Value Δ	Absolute		
			Min	Max	
Operating Supply Current	I_i	± 0.25	-	17	mA
Output Voltage	V_{REF}	± 0.025	4.95	5.05	V
Output Low Level	V_{OL2}	± 0.05	-	2.2	V
Output High Level	V_{OH2}	± 0.05	12	-	V

2.6 HIGH TEMPERATURE REVERSE BIAS BURN-IN CONDITIONS

Characteristics	Symbols	Test Conditions	Units
Ambient Temperature	T_{amb}	+100 (+0 -5)	$^{\circ}\text{C}$
Supply Voltage	V_i	30	V
Junction Temperature	T_j	+150 (+0 -5)	$^{\circ}\text{C}$
Duration	t	≥ 168	Hours

NOTES:

1. High Temperature Reverse Bias Burn-in may be carried out using the following test circuit:



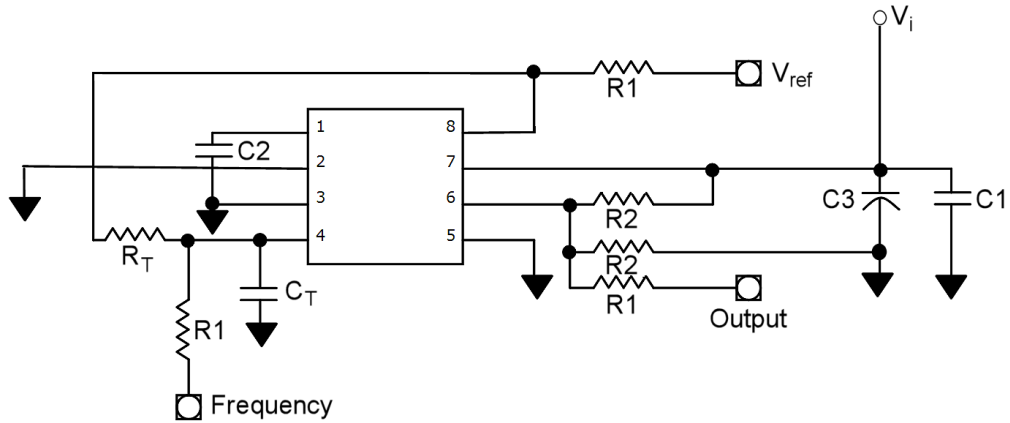
$R0 = 0\Omega$ $C1 = 1nF$
 $R1 = 10k\Omega$ $C2 = 100nF$
 $R2 = 1k\Omega$

2.7 **POWER BURN-IN CONDITIONS**

Characteristics	Symbols	Test Conditions	Units
Ambient Temperature	T_{amb}	+125 (+0 -5)	°C
Supply Voltage	V_i	18	V
Frequency	f	350	kHz
Junction Temperature	T_j	+150 (+0 -5)	°C

NOTES:

1. Power Burn-in may be carried out using the following test circuit:



$R_T = 10k\Omega$ $C_T = 470pF$
 $R1 = 1k\Omega$ $C1 = 100nF$
 $R2 = 100k\Omega$ $C2 = 1\mu F$
 $C3 = 470\mu F$

2.8 **OPERATING LIFE CONDITIONS**

The conditions shall be as specified in Para. 2.7 for Power Burn-in.

2.9 TOTAL DOSE RADIATION TESTING

2.9.1 Bias Conditions and Total Dose Level for Total Dose Radiation Testing

Irradiation testing shall be carried out at Dose Rate Window 2 ("Low Rate"): 36 to 360 rad hr⁻¹.

No bias shall be applied during irradiation testing (all pins connected to Ground).

The total dose level applied shall be as specified in Para. 1.4.2 Component Type Variants or in the Purchase Order.

2.9.2 Electrical Measurements for Total Dose Radiation Testing

Prior to irradiation testing the devices shall have successfully met Para. 2.3.1 Room Temperature Electrical Measurements.

Unless otherwise stated the measurements shall be performed at T_{amb} = +22 ±3°C.

The test methods and test conditions shall be as per the corresponding test defined in Para. 2.3.1 Room Temperature Electrical Measurements.

The parameters to be measured during and on completion of irradiation testing are shown below.

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions	Limits		Units
				Min	Max	
REFERENCE SECTION						
Output Voltage	V _{REF}	-	V _i = 15V R _T = 10kΩ, C _T = 3.3nF I _o = 1mA	4.85	5.15	V
Line regulation	ΔV _{REF_LINE}	-	12V ≤ V _i ≤ 25V R _T = 10kΩ, C _T = 3.3nF	-	20	mV
Load Regulation	ΔV _{REF_LOAD}	-	V _i = 15V R _T = 10kΩ, C _T = 3.3nF 1mA ≤ I _o ≤ 20mA	-	25	mV
Output Short Circuit Current	I _{sc}	3011	V _i = 15V R _T = 10kΩ, C _T = 3.3nF	-180	-30	mA
OSCILLATOR SECTION						
Frequency	f _{osc}	-	V _i = 15V R _T = 10kΩ, C _T = 3.3nF	49	65	kHz
Frequency Change with Voltage	Δf _{osc} /ΔV	-	12V ≤ V _i ≤ 25V R _T = 10kΩ, C _T = 3.3nF	-1	1	%
Discharge Current	I _{DISCHG}	-	V _i = 15V R _T = 10kΩ, C _T = 3.3nF V _{osc} = 2V	7.8	8.8	mA

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions	Limits		Units
				Min	Max	
ERROR AMP SECTION						
Input Voltage	V ₂	-	V _i = 15V R _T = 10kΩ, C _T = 3.3nF V _{PIN1} = 2.5V	2.45	2.6	V
Input Bias Current	I _b	4001	V _i = 15V R _T = 10kΩ, C _T = 3.3nF V _{FB} = 5V	-2.75	2.75	μA
Open Loop Voltage Gain	A _{VOL}	-	V _i = 15V R _T = 10kΩ, C _T = 3.3nF 2V ≤ V _O ≤ 4V	60	-	dB
Power Supply Rejection Ratio	PSRR	4003	12V ≤ V _i ≤ 25V R _T = 10kΩ, C _T = 3.3nF	60	-	dB
Output Sink Current	I _{O_SINK}	-	V _i = 15V R _T = 10kΩ, C _T = 3.3nF V _{PIN2} = 2.7V V _{PIN1} = 1.1V	2	-	mA
Output Source Current	I _{O_SOURCE}	-	V _i = 15V R _T = 10kΩ, C _T = 3.3nF V _{PIN2} = 2.3V V _{PIN1} = 5V	-	-500	μA
V _{OUT} High	V _{OH}	-	V _i = 15V R _T = 10kΩ, C _T = 3.3nF V _{PIN2} = 2.3V R _L = 15kΩ to GROUND	5	-	V
V _{OUT} Low	V _{OL}	-	V _i = 15V R _T = 10kΩ, C _T = 3.3nF V _{PIN2} = 2.3V R _L = 15kΩ to V _{ref}	-	1.1	V
CURRENT SENSE SECTION						
Gain	G _V	4004	V _i = 15V R _T = 10kΩ, C _T = 3.3nF Notes 1, 2	2.85	3.15	V/V
Maximum Input Signal	V ₃	-	V _i = 15V R _T = 10kΩ, C _T = 3.3nF V _{PIN1} = 2.3V Note 1	0.9	1.1	V
Supply Voltage Rejection	SVR	-	12V ≤ V _i ≤ 25V R _T = 10kΩ, C _T = 3.3nF Note 1	60	-	dB
Input Bias Current	I _b	4001	V _i = 15V R _T = 10kΩ, C _T = 3.3nF	-50	50	μA
Delay to output	d _o	3003	V _i = 15V R _T = 10kΩ, C _T = 3.3nF	-	300	ns

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions	Limits		Units
				Min	Max	
OUTPUT SECTION						
Output Low Level	V _{OL1}	3007	V _i = 15V R _T = 10kΩ, C _T = 3.3nF I _{SINK} = 20mA	-	400	mV
Output Low Level	V _{OL2}	3007	V _i = 15V R _T = 10kΩ, C _T = 3.3nF I _{SINK} = 200mA	-	2.2	V
Output High level	V _{OH1}	3006	V _i = 15V R _T = 10kΩ, C _T = 3.3nF I _{SOURCE} = 20mA	13	-	V
Output High Level	V _{OH2}	3006	V _i = 15V R _T = 10kΩ, C _T = 3.3nF I _{SOURCE} = 200mA	12	-	V
UVLO Saturation	V _{OLS}	-	V _i = 6V R _T = 10kΩ, C _T = 3.3nF I _{SINK} = 1mA	-	1.1	V
Rise Time	t _r	3004	V _i = 15V R _T = 10kΩ, C _T = 3.3nF C _L = 1nF	-	180	ns
Fall Time	t _f	3004	V _i = 15V R _T = 10kΩ, C _T = 3.3nF C _L = 1nF	-	180	ns
UNDER-VOLTAGE LOCKOUT SECTION						
Start Threshold	V _{TH}	-	V _i = 15V R _T = 10kΩ, C _T = 3.3nF	7.8	9.5	V
Min Operating Voltage after Turn-on	V _{MIN}	-	V _i = 15V R _T = 10kΩ, C _T = 3.3nF	7	8.6	V
Max Duty Cycle	DC _{MAX}	-	V _i = 15V R _T = 10kΩ, C _T = 3.3nF	94	100	%
Min Duty Cycle	DC _{MIN}	-	V _i = 15V R _T = 10kΩ, C _T = 3.3nF	-	0	%
TOTAL STAND-BY CURRENT						
Start-up current	I _{ST}	-	V _i = 6.5V R _T = 10kΩ, C _T = 3.3nF	-	500	μA
Operating Supply Current	I _i	3005	V _i = 15V R _T = 10kΩ, C _T = 3.3nF V _{PIN2} = V _{PIN3} = 0V	-	17	mA
Zener Voltage	V _{IZ}	-	V _i = 15V R _T = 10kΩ, C _T = 3.3nF I _i = 25mA	30	-	V

APPENDIX 'A'
AGREED DEVIATIONS FOR STMICROELECTRONICS (F)

ITEMS AFFECTED	DESCRIPTION OF DEVIATIONS
Para. 2.1.1 Deviation from the Generic Specification: Deviations from Screening Tests - Chart F3	External Visual Inspection: The criteria applicable to chip-outs are those described in MIL-STD-883 , Test Method 2009 , Paras 3.3.6(b) and 3.3.7(a).
Para. 2.1.1 Deviation from the Generic Specification: Deviations from Qualification and Periodic Tests - Chart F4	External Visual Inspection: The criteria applicable to chip-outs are those described in MIL-STD-883 , Test Method 2009 , Paras 3.3.6(b) and 3.3.7(a). Operating Life: The temperature limits of MIL-STD-883 , Para. 4.5.8(c) may be used.

ADDITIONAL DATA – STMICROELECTRONICS (F)

- (a) Single Event Effects (SEE) Information
 These components are susceptible to Single Event Latch-up (SEL) and Single Event Transient (SET) if operated in a space environment.

Typical performance:

- SEL immunity at 30V, +125°C and 60° tilt: 120MeV/cm²
- SET threshold: 1.5MeV/mg/cm²; Saturated Cross Section: 1 x10⁻²cm²

For more information on SEE performance, contact STMicroelectronics.